

**B. Tech.**
**(Semester-II) Theory Examination 2017 - 18**
**ENGINEERING PHYSICS-II**
**Time:3 Hours**
**Total Marks:70**
**Note:** Attempt all Sections. If require any missing data then choose suitably.

**SECTION A**

1. Attempt *all* questions in brief. 2 x 7 = 14
- Define unit cell and primitive cell.
  - Find out the packing factor for a Simple Cubic structure.
  - What is ionic polarization in dielectrics?
  - What is the origin of magnetization in magnetic materials?
  - What is the difference between conduction current and displacement current?
  - What do you mean by intrinsic and extrinsic semiconductors?
  - Explain effect of temperature on electrical resistivity of superconducting materials.

**SECTION B**

2. Attempt any *three* parts of the following: 7 x 3 = 21
- Derive an expression for Compton shift. Explain the presence of unmodified radiation in Compton scattering.
  - Explain ferroelectricity and piezoelectricity. Give some applications of ferroelectric and piezoelectric materials.
  - Derive the electromagnetic wave equations in free space. Prove that the electromagnetic waves propagate with speed of light in free space.
  - Show that the Fermi level of an intrinsic semiconductor lies half way between conduction band and valance band. What will be position of Fermi level in n-type semiconductor? Explain with suitable diagram.
  - What are carbon nanotubes? Discuss arm chair, zigzag and chiral single walled carbon nanotubes

**SECTION C**

3. Attempt any *one* part of the following: 7 x 1 = 7
- Show that in a cubic lattice the distance between successive planes of indices (h k l) is given by  $d_{hkl} = \frac{a}{\sqrt{h^2+k^2+l^2}}$ , where 'a' is lattice constant. A substance with FCC lattice has density  $6250\text{-kg/m}^3$  and molecular weight 60.2. Calculate the lattice constant. Given, Avogadro's number is  $6.02 \times 10^{23}$  per gm molecule.
  - What is Laue's spot in X-ray diffraction? Explain how Bragg's law explained formation of Laue's spot? Calculate the longest wavelength that can be analyzed by a crystal of spacing  $2.82 \text{ \AA}$  in the second order.

4. **Attempt any one part of the following:** 7 x 1 = 7
- (a) Explain dielectric loss. Deduce an expression for dielectric loss and sketch the loss spectrum for a polar material.
- (b) Distinguish diamagnetic, paramagnetic and ferromagnetic substances. A material has 10 turns per cm of wire wound uniformly upon it which carries a current of 2.0 ampere. The flux density in the material is 1.0 Weber/m<sup>2</sup>. Calculate the magnetization of material ( $\mu_0 = 4\pi \times 10^{-7}$  weber/amp-meter).
5. **Attempt any one part of the following:** 7 x 1 = 7
- (a) Derive Maxwell's equations in differential form. Give physical significance of each equation.
- (b) Prove that electromagnetic waves are transverse in nature. If the magnitude of  $E$  in a plane electromagnetic wave is 377 V/m, determine the magnitude of  $H$  in free space.
6. **Attempt any one part of the following:** 7 x 1 = 7
- (a) Find out the probability of occupancy of an energy level by an electron if (i)  $E < E_F$  and (ii)  $E > E_F$ , where  $E_F$  is Fermi energy. Calculate the probability of occupancy of energy level by an electron at 300K which is lying 0.015eV below Fermi-level.
- (b) Deduce an expression for the concentration of electrons in conduction band of an intrinsic semiconductor. A semiconductor rod of 10 mm length and 1 mm<sup>2</sup> cross-section has been doped with a total of  $5 \times 10^{13}$  donor atoms at room temperature. Calculate the electron and hole densities if the intrinsic carrier density in semiconductor is  $2.4 \times 10^{19} \text{ m}^{-3}$ .
7. **Attempt any one part of the following:** 7 x 1 = 7
- (a) Discuss Meissner effect. Show that perfect diamagnetism and zero resistivity are two independent and essential properties of the superconductor.
- (b) Explain superconductivity on the basis of BCS theory. Determine critical current and current density, which can flow through a long thin superconducting wire of diameter 2 mm if critical field for the material is  $1.2 \times 10^4$  A/m.